

METHOD OF FABRICATING A FINFET

Abstract

A FinFET structure and method of forming a FinFET device. The method includes: (a) providing a semiconductor substrate, (b) forming a dielectric layer on a top surface of the substrate; (c) forming a silicon fin on a top surface of the dielectric layer; (d) forming a protective layer on at least one sidewall of the fin; and (e) removing the protective layer from the at least one sidewall in a channel region of the fin. In a second embodiment, the protective layer is converted to a protective spacer.